

800V N-Channel Super Junction Power MOSFET

Description:

This series of power MOSFET use N channel Multi-EPI Super-Junction technology and design to provide better characteristics, such as fast switching time, low Ciss and Crss, low on resistance and excellent avalanche characteristics, making it especially suitable for applications which require superior power density and outstanding efficiency.

Features:

- Low on-resistance
- Ultra low gate charge and input capacitance
- 100% avalanche tested
- Rohs compliant

Mechanical Data:

- Case: TO-220, ITO-220, TO-263, TO-262, TO-251, TO-252 Package

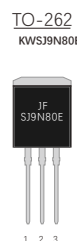
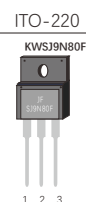
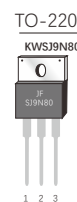
Application:

- Switching applications

Ordering Information

Part No.	Package Type	Package	Quality(box)
KWSJ9N80	TO-220	Tube	1000
KWSJ9N80F	ITO-220	Tube	1000
KWSJ9N80D	TO-263	Tape & Reel	800
KWSJ9N80E	TO-262	Tube	1000
KWSJ9N80N	TO-251	Tube	1000
KWSJ9N80M	TO-252	Tape & Reel	3000

Product Summary			
V _{DS}	R _{DS(on)} (Ω)Typ	I _D (A)	Q _g (Typ)
800V	0.55 @ 10V, 4.5A	9.0	38nc



Block Diagram

Pin Definition:

1. Gate
2. Drain
3. Source

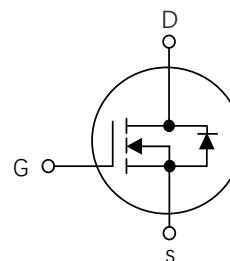


Table1 Absolute Maximum Ratings (T_c=25° C, unless otherwise specified)

Parameters		Symbol	KWSJ9N80 KWSJ9N80D KWSJ9N80E	KWSJ9N80M KWSJ9N80N	KWSJ9N80F	Unit
Drain-Source Voltage		V _{DS}	800			V
Gate-Source Voltage		V _{GS}	±30			V
Contionous Drain Current	T _C =25°C	I _D	9			A
	T _C =100°C		6			
Pulsed Drain Current (Note 1)		I _{DM}	36			A
Single Pulse Avalanche Energy(Note 2)		EAS	290			mJ
Avalanche Current(Note 1)		I _{AR}	2.8			A
Repetitive Avalanche Energy(Note 1)		EAR	1.4			mJ
Reverse Diode Recovery dv/dt(Note 3)		dv/dt	15			V/ns
Drain Source Voltage Slope (V _{DS} =720V)		dv/dt	50			V/ns
Power Dissipation T _C =25°C		P _D	131		34	W
Operating Junction and Storage Temperature		T _J /T _{STG}	-55 ~ +150			°C

Table 2. Thermal Characteristics

Parameters	Symbol	KWSJ9N80 KWSJ9N80D KWSJ9N80E	KWSJ9N80M KWSJ9N80N	KWSJ9N80F	Unit
Thermal resistance Junction to Ambient	$R_{\theta JA}$	62.5		80.0	$^{\circ}\text{C}/\text{W}$
Thermal resistance Junction to Case	$R_{\theta JC}$	0.95		3.70	$^{\circ}\text{C}/\text{W}$

Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise specified)

Parameters		Symbol	Test Conditions	Min	Typ	Max	Unit
Off Characteristics							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V,I _D =250μA	800			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =800V,V _{GS} =0V			1	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =30V,V _{DS} =0V			100	nA
	Reverse		V _{GS} = -30V,V _{DS} =0V			-100	nA
On Characteristics(Note 4)							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} ,I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V,I _D =5.0A		0.55	0.60	Ω
Dynamic Characteristics(Note 5)							
Input Capacitance		C _{ISS}	V _{DS} =25V,V _{GS} =0V,f=1MHz		680		pF
Output Capacitance		C _{OSS}			60		pF
Reverse Transfer Capacitance		C _{RSS}			15		pF
Switching Characteristics (Note 5)							
Turn-On Delay Time		td(on)	V _{DD} =400V,I _D =5A, V _{GS} =10V,R _G =20Ω		15		ns
Turn-On Rise Time		tr			10		ns
Turn-Off Delay Time		td(off)			110		ns
Turn-Off Fall Time		tf			10		ns
Total Gate Charge		Q _G	V _{DS} =480V,I _D =5A, V _{GS} =10V		38		nC
Gate-Source Charge		Q _{GS}			4		nC
Gate-Drain Charge		Q _{GD}			4.5		nC
Drain-Source Diode Characteristics and Maximum Ratings							
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} =0V,I _S =5A		1.0	1.5	V
Maximum Continuous Drain-Source Diode Forward Current(Note 4)		I _S				36	A
Reverse Recovery Time		trr	V _R =400V,I _S =5.0A		475		ns
Reverse Recovery Charge		Q _{RR}	dI _F /dt=100A/μs(Note 4)		5800		nC

Notes: 1 Repetitive Rating:Pulse width limited by maximum junction temperature
2 $R_G=25\Omega, V_G=10V, V_{DD}=50V$, Starting $T_J=25^{\circ}\text{C}$
3 $I_{SD}\leq I_D, di/dt\leq 200A/\mu s, V_{DD}\leq BV_{DSS}$, starting $T_J=25^{\circ}\text{C}$
4 Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
5 Guaranteed by design, not subject to production

Typical Characteristics Diagrams

Figure 1. Output Characteristics

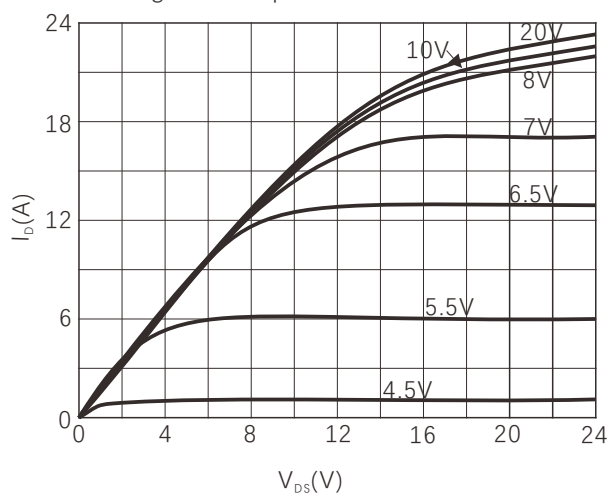


Figure 2. Transfer Characteristics

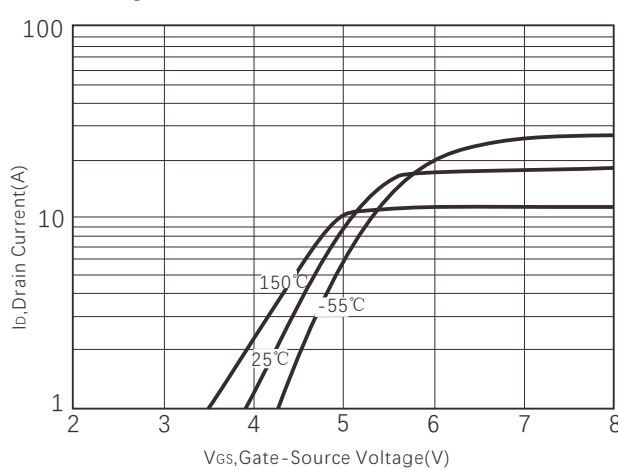


Figure 3. On-Resistance vs. Drain Current

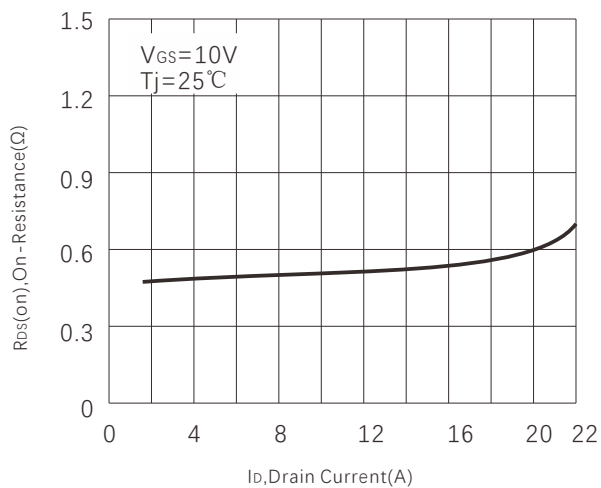


Figure 4. Capacitance

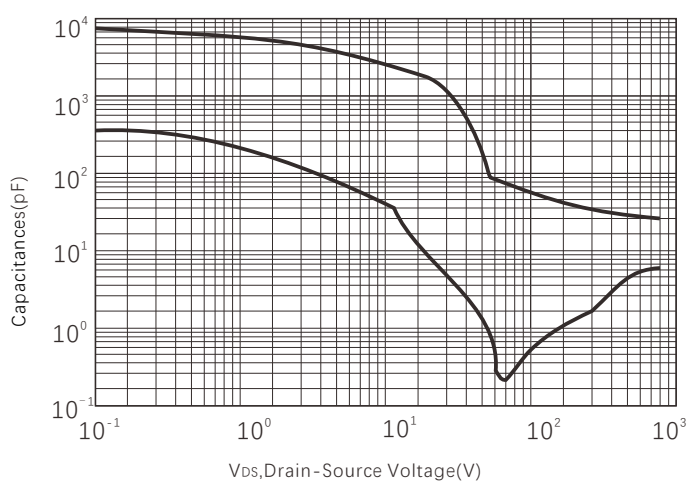


Figure 5. Gate charge

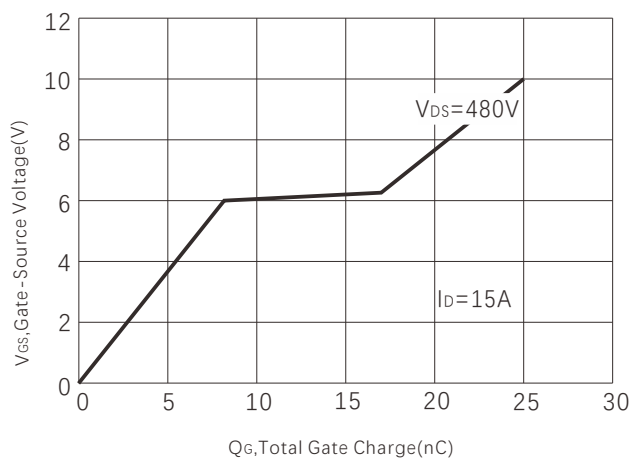


Figure 6. Source-Drain Diode Forward Voltage

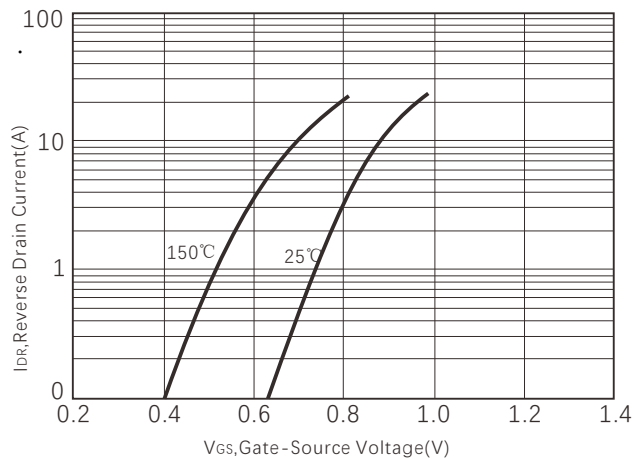


Figure 7. $R_{DS(ON)}$ vs Junction Temperature

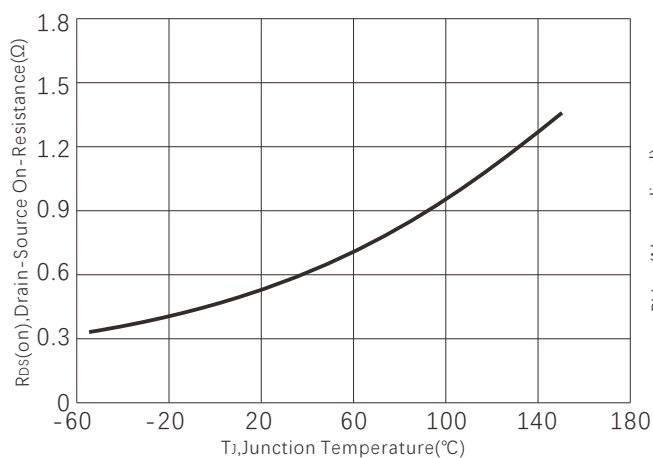


Figure 8. BV_{DSS} vs Junction Temperature

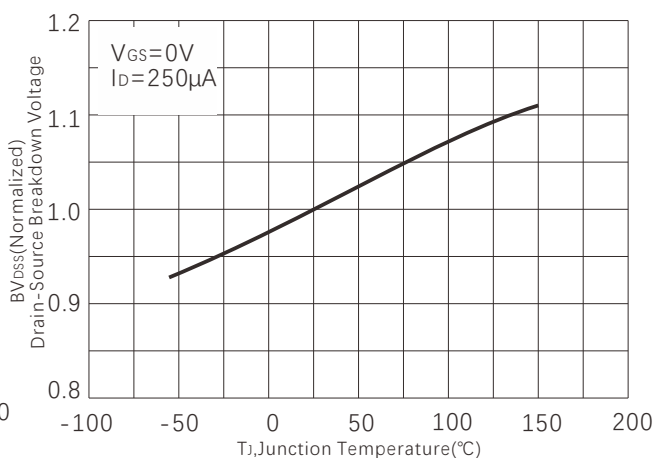


Figure 9. Safe operating area

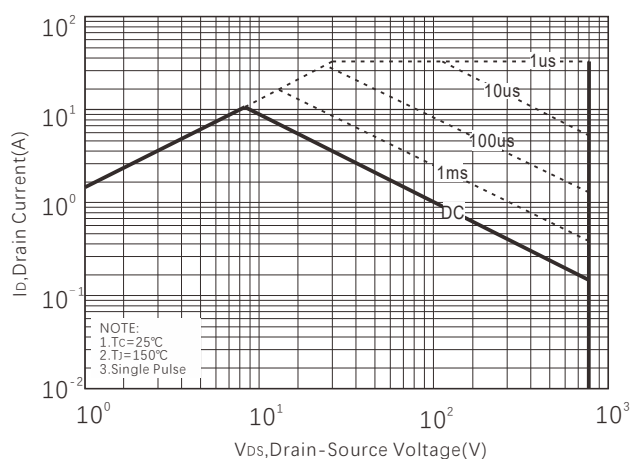


Figure 10. Safe operating area for ITO-220

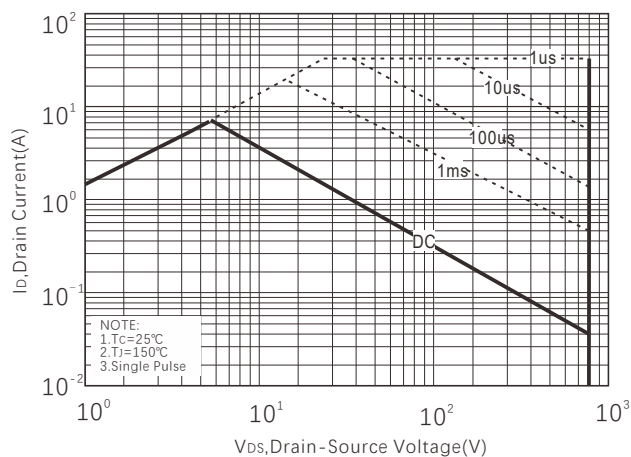
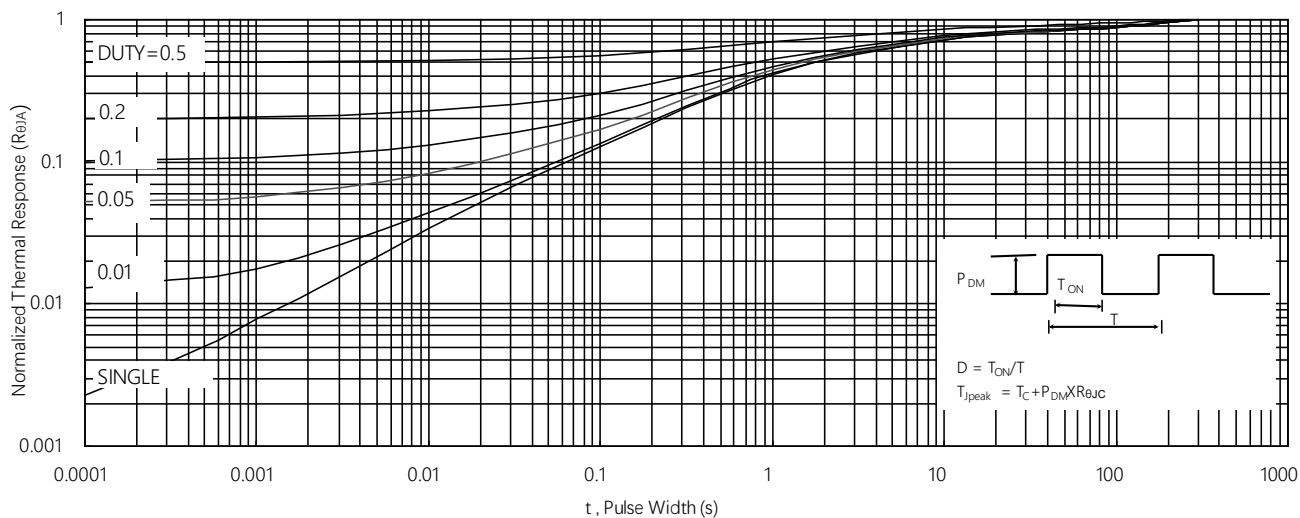
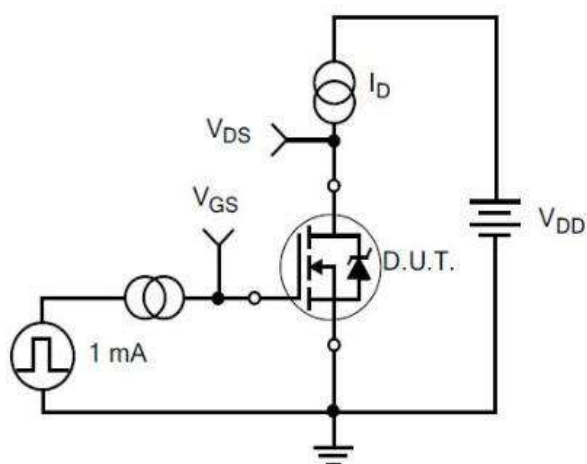


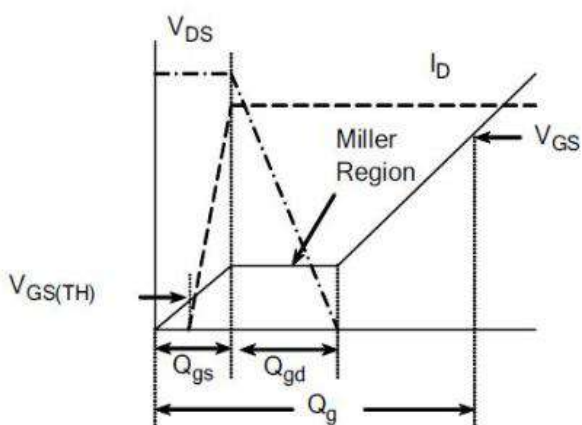
Figure 11. Normalized Maximum Transient Thermal Impedance



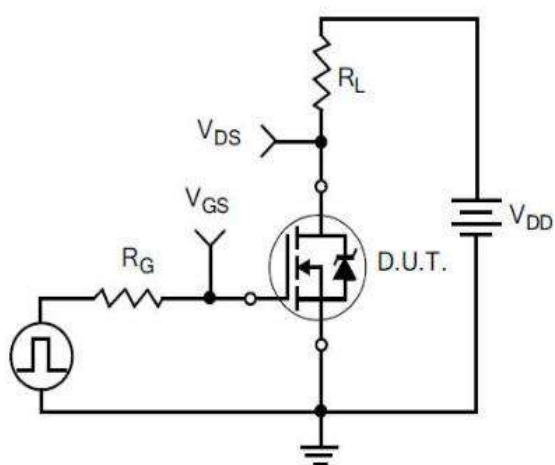
Typical Test Circuit



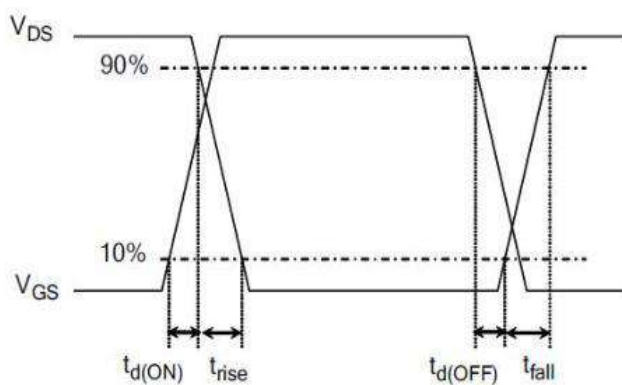
1) Gate Charge Test Circuit



2) Gate Charge Waveform

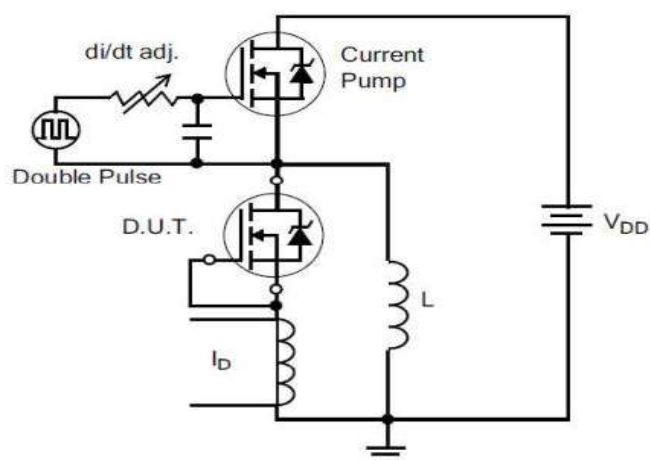


3) Resistive Switching Test Circuit

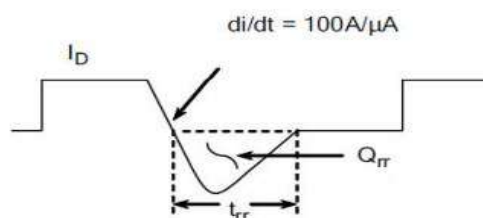


4) Resistive Switching Waveforms

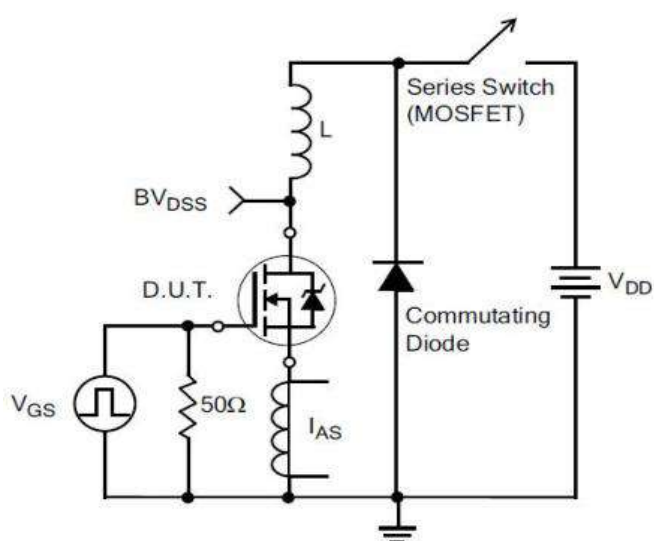
Typical Test Circuit



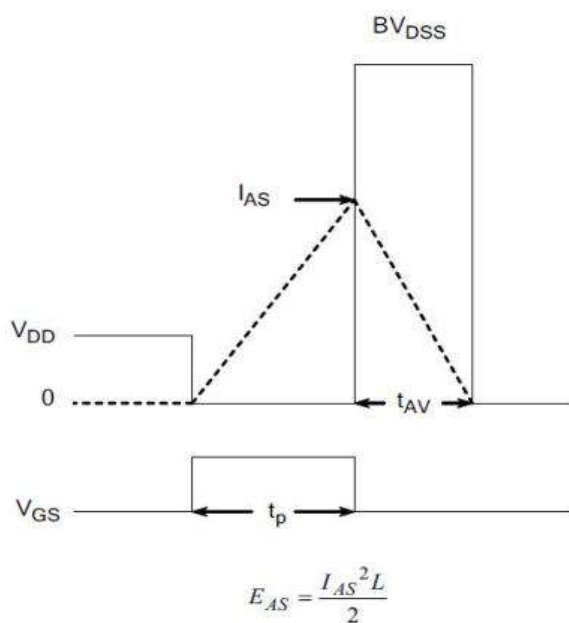
5) Diode Reverse Recovery Test Circuit



6) Diode Reverse Recovery Waveform

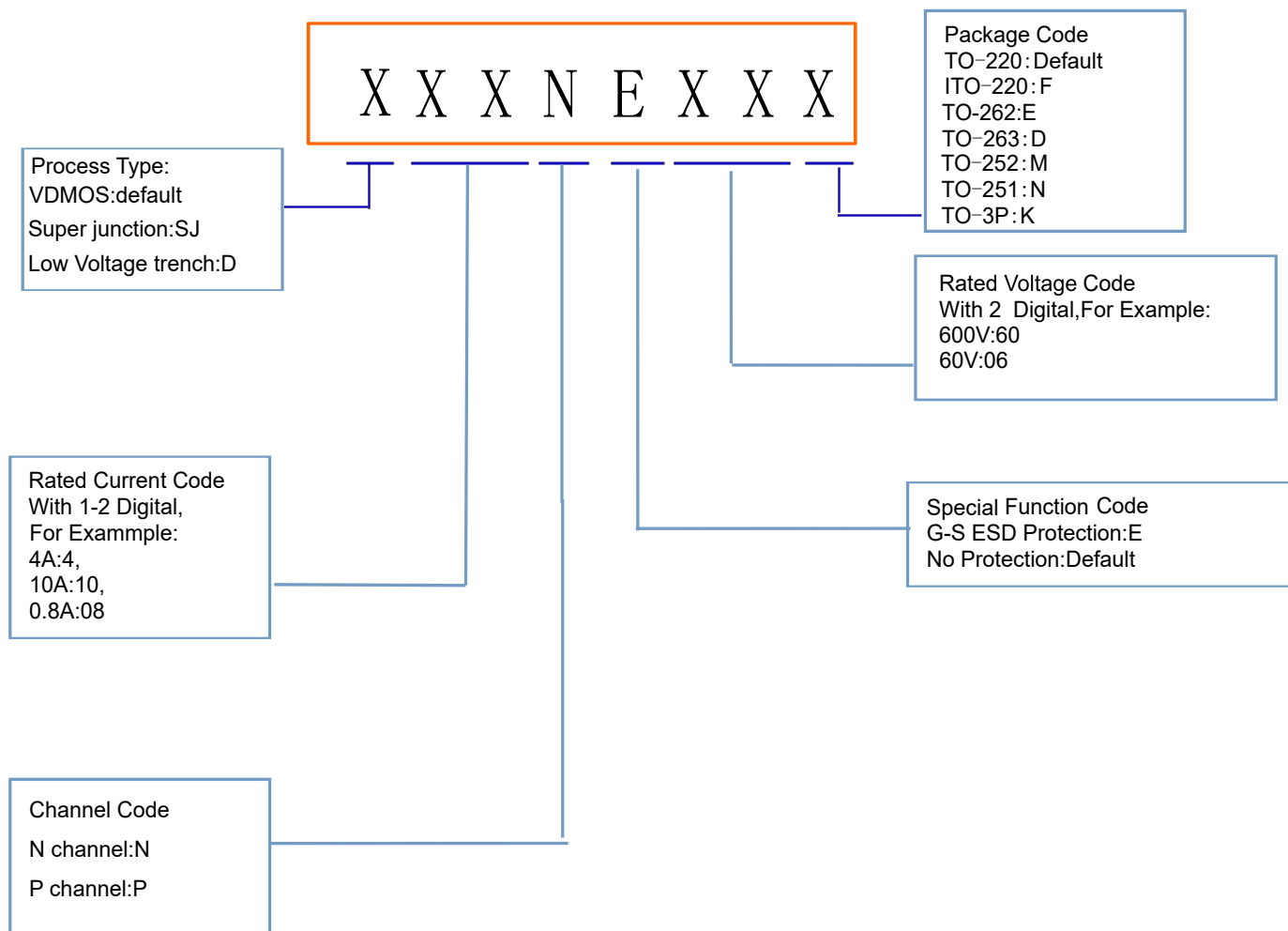


7) . Unclamped Inductive Switching Test Circuit



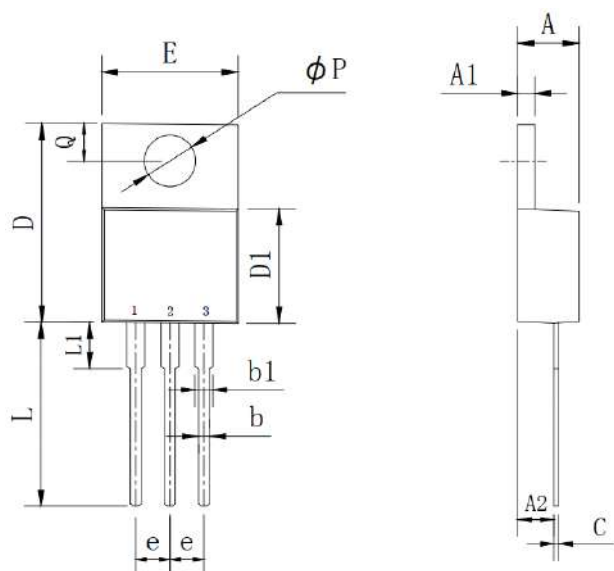
8) Unclamped Inductive Switching Waveforms

Product Names Rules



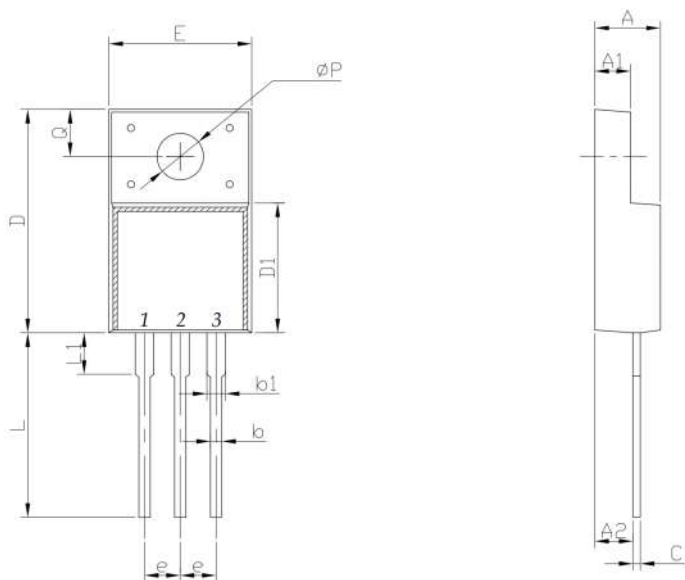
Dimensions

TO-220 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	4.25	4.87	0.167	0.192
A1	1.07	1.47	0.042	0.058
A2	2.03	2.92	0.080	0.115
b	0.51	1.11	0.020	0.044
b1	0.97	1.6	0.038	0.063
C	0.3	0.7	0.012	0.028
D	14.6	15.9	0.575	0.626
D1	8.04	9.3	0.317	0.366
E	9.57	10.57	0.377	0.416
e	2.34	2.74	0.092	0.108
L	12.58	14.3	0.495	0.563
L1	2.8	4.2	0.110	0.165
P	3.4	4.14	0.134	0.163
Q	2.45	3	0.096	0.118

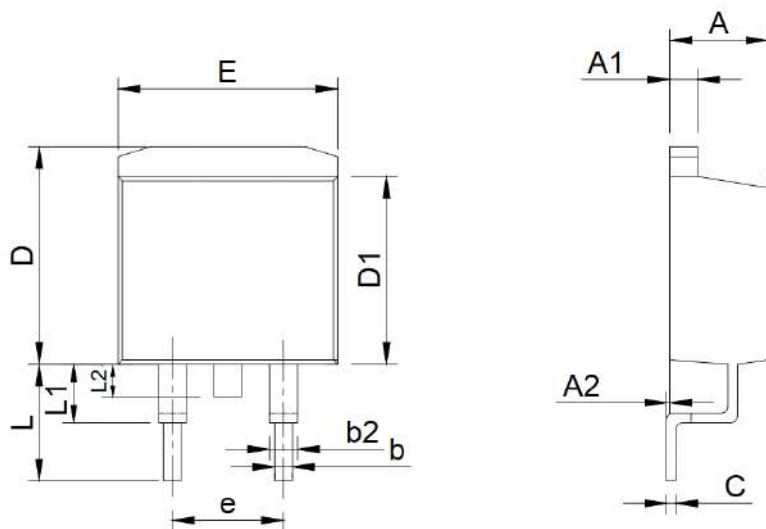
ITO-220 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	4.24	4.9	0.167	0.193
A1	2.3	2.92	0.091	0.115
A2	2.61	2.81	0.103	0.111
b	0.3	1	0.012	0.039
b1	0.9	1.55	0.035	0.061
C	0.3	0.7	0.012	0.028
D	14.5	16.36	0.571	0.644
D1	8.8	9.41	0.346	0.370
E	9.5	10.5	0.374	0.413
e	2.3	2.75	0.091	0.108
L	12.6	14	0.496	0.551
L1	2.45	4.3	0.096	0.169
P	2.9	3.8	0.114	0.150
Q	2.5	3.55	0.098	0.140

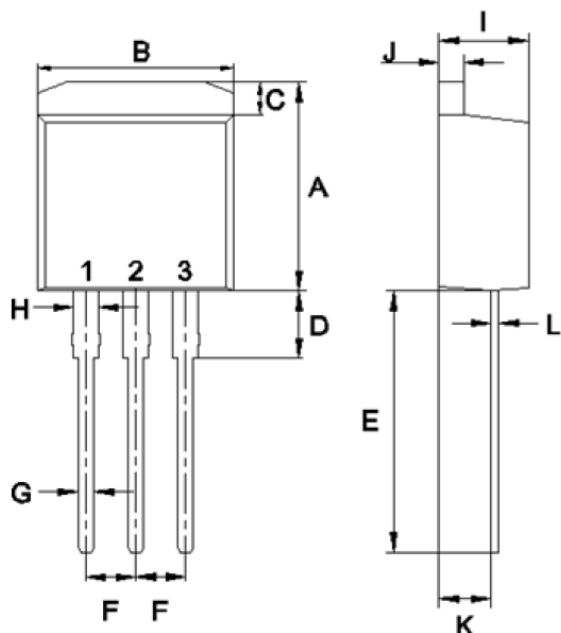
Dimensions

TO-263 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	4.25	4.87	0.167	0.192
A1	1.07	1.47	0.042	0.058
A2	0	0.25	0.000	0.010
b	0.61	1.01	0.024	0.040
b1	1.2	1.34	0.047	0.053
C	0.3	0.6	0.012	0.024
D	9.48	10.84	0.373	0.427
D1	8.49	9.3	0.334	0.366
E	9.7	10.31	0.382	0.406
e	4.88	5.28	0.192	0.208
L	4.46	5.85	0.176	0.230
L1	1.33	2.33	0.052	0.092
L2	0	2.2	0.000	0.087

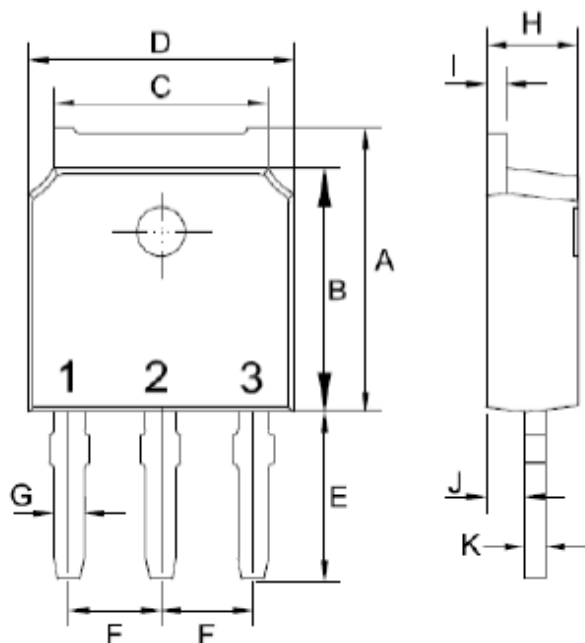
TO-262 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	10.14	11.14	0.399	0.439
B	9.57	10.57	0.377	0.416
C	1.15	1.84	0.045	0.072
D	2.95	3.95	0.116	0.156
E	12.25	13.75	0.482	0.541
F	2.34	2.74	0.092	0.108
G	0.51	1.11	0.020	0.044
H	0.97	1.57	0.038	0.062
I	4.25	4.87	0.167	0.192
J	1.07	1.47	0.042	0.058
K	2.03	2.92	0.080	0.115
L	0.3	0.6	0.012	0.024

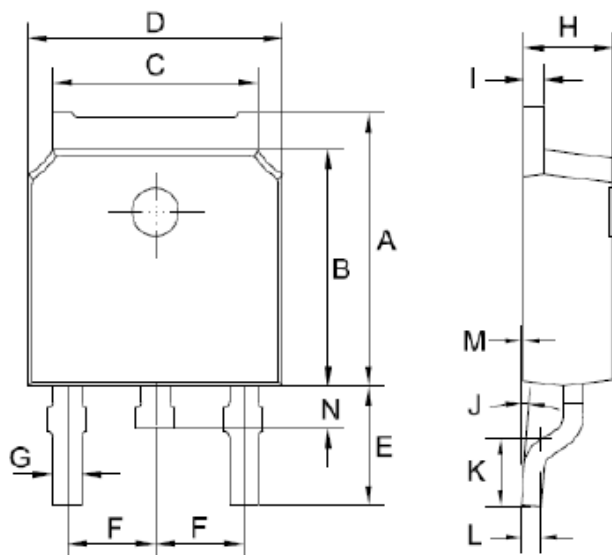
Dimensions

TO-251 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	6.85	7.25	0.270	0.285
B	5.8	6.3	0.228	0.248
C	5	5.53	0.197	0.218
D	6.3	6.8	0.248	0.268
E	3.5	4.35	0.138	0.171
F	2.19	2.39	0.086	0.094
G	0.45	0.85	0.018	0.033
H	2.2	2.4	0.087	0.094
I	0.41	0.61	0.016	0.024
J	0.71	1.31	0.028	0.052
K	0.41	0.61	0.016	0.024

TO-252 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	6.85	7.25	0.270	0.285
B	5.8	6.3	0.228	0.248
C	5	5.53	0.197	0.218
D	6.3	6.8	0.248	0.268
E	2.6	3.3	0.102	0.130
F	2.19	2.39	0.086	0.094
G	0.45	0.85	0.018	0.033
H	2.2	2.4	0.087	0.094
I	0.41	0.61	0.016	0.024
J	0.41	0.81	0.016	0.032
K	1.45	1.85	0.057	0.073
L	0.41	0.61	0.016	0.024
M	0	0.12	0.000	0.005
P	0.6	1	0.024	0.039